ZEISS Gemini Optics
High Resolution Images On Real World Samples

Mesoporous silica. Imaged with Inlens SE detector at 500V.

Nanometer spaced FeO(OH) crystals. Imaged with Inlens SE detector at 1kV.

Platinum nanostructures sputtered on nickel dendrites. Imaged with Inlens SE at 1.5kV.

Gold nanoparticles on polystyrol sphere. Imaged simultaneously at 3kV. Left: Inlens SE image, surface topography. Right: EsB image, material contrast.

45nm semiconductor device imaged with annular-STEM. The diffraction contrast in brightfield (BF) and darkfield (DF) images reveal damaged crystal lattice at ion implanted Si regions. High-angle annular darkfield (HAADF) captures mass scattering effect to give highest contrast of the silicide.

Moth wing. Inlens SE detector, at 50V, in high vacuum. No charging effect if ultra-low voltage like 50V is applied.

FinFET transistor. Top view, 22nm technology, pure BSE imaging using EsB, at 3kV with high material contrast.

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